

FGW40N120WD

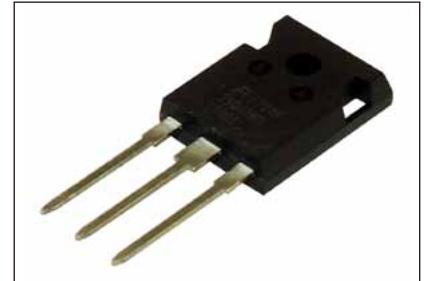
Discrete IGBT (High-Speed W series) 1200V / 40A

■ Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)

■ Applications

- Uninterruptible power supply
- PV Power conditioner
- Inverter welding machine



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

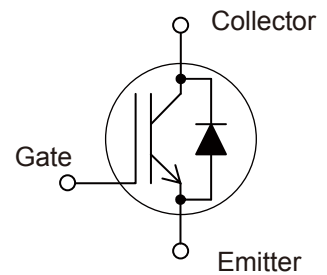
Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter voltage	V _{CEs}	1200	V	
Gate-Emitter voltage	V _{GES}	±20	V	
DC Collector Current	I _{C@25} I _{C@100}	65 40	A	T _c =25°C, T _j =150°C T _c =100°C, T _j =150°C
Pulsed Collector Current	I _{CP}	160	A	Note *1
Turn-Off Safe Operating Area	-	160	A	V _{CE} ≤1200V, T _j ≤175°C
Diode Forward Current	I _{F@25} I _{F@100}	36 20	A	
Diode Pulsed Current	I _{FP}	160	A	Note *1
Short Circuit Withstand Time	t _{sc}	5	μs	V _{CC} ≤600V, V _{GE} =15V T _j ≤150°C
IGBT Max. Power Dissipation	P _{D_IGBT}	430	W	T _c =25°C
FWD Max. Power Dissipation	P _{D_FWD}	125	W	T _c =25°C
Operating Junction Temperature	T _j	-40~+175	°C	
Storage Temperature	T _{stg}	-55~+175	°C	

Note *1 : Pulse width limited by T_{jmax}.

● Electrical characteristics (at T_j= 25°C unless otherwise specified)

Description	Symbols	Conditions	Characteristics			Unit	
			min.	typ.	max.		
Zero Gate Voltage Collector Current	I _{CES}	V _{CE} = 1200V, V _{GE} = 0V	T _j =25°C	-	-	250	μA
			T _j =175°C	-	-	2	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	200	nA	
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 20V, I _C = 40mA	5.0	6.0	7.0	V	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} = 15V, I _C = 40A	T _j =25°C	-	2.0	2.6	V
			T _j =175°C	-	2.6	-	
Input Capacitance	C _{ies}	V _{CE} =25V	-	2500	-	pF	
Output Capacitance	C _{oes}	V _{GE} =0V	-	110	-		
Reverse Transfer Capacitance	C _{res}	f=1MHz	-	34	-		
Gate Charge	Q _G	V _{CC} = 400V I _C = 40A V _{GE} = 15V	-	120	-	nC	
Turn-On Delay Time	t _{d(on)}	T _j = 25°C	-	32	-	ns	
Rise Time	t _r	V _{CC} = 600V	-	54	-		
Turn-Off Delay Time	t _{d(off)}	I _C = 40A	-	178	-		
Fall Time	t _f	V _{GE} = 15V	-	40	-		
Turn-On Energy	E _{on}	R _G = 10Ω L = 500μH	-	2.8	-	mJ	
Turn-Off Energy	E _{off}	Energy loss include "tail" and FWD (FDRW20S120J) reverse recovery.	-	1.6	-		
Turn-On Delay Time	t _{d(on)}	T _j = 150°C	-	32	-	ns	
Rise Time	t _r	V _{CC} = 600V	-	48	-		
Turn-Off Delay Time	t _{d(off)}	I _C = 40A	-	220	-		
Fall Time	t _f	V _{GE} = 15V	-	56	-		
Turn-On Energy	E _{on}	R _G = 10Ω L = 500μH	-	4.6	-	mJ	
Turn-Off Energy	E _{off}	Energy loss include "tail" and FWD (FDRW20S120J) reverse recovery.	-	2.4	-		
Forward Voltage Drop	V _F	I _F =20A	T _j =25°C	-	2.2	2.8	V
			T _j =175°C	-	1.8	-	V
Diode Reverse Recovery Time	t _{rr1}	V _{CC} =30V I _F = 3.0A -di/dt=200A/μs	-	42	-	ns	
Diode Reverse Recovery Time	t _{rr2}	V _{CC} =600V I _F =20A	-	0.38	-	μs	
Diode Reverse Recovery Charge	Q _{rr}	-di _F /dt=200A/μs T _j =25°C	-	0.95	-	μC	

■ Equivalent circuit



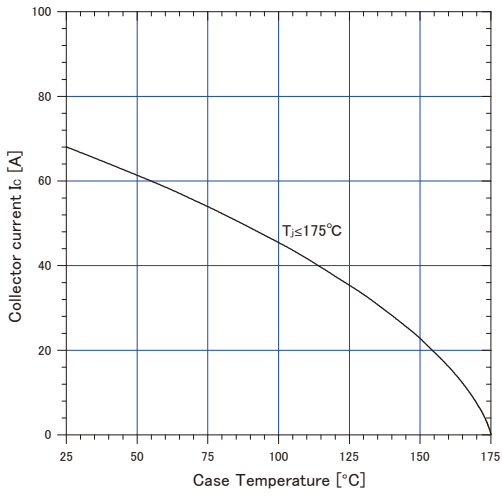
Description	Symbols	Conditions	Characteristics			Unit
			min.	typ.	max.	
Diode Reverse Recovery Time	t_{rr2}	$V_{CC}=600V$ $I_F=20A$	-	0.66	-	μs
Diode Reverse Recovery Charge	Q_{rr}	$-di_F/dt=200A/\mu s$ $T_j=175^\circ C$	-	4.5	-	μC

● **Thermal resistance**

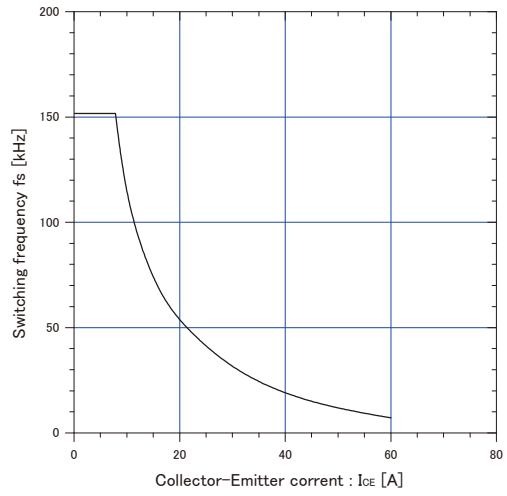
Items	Symbols	Characteristics			Unit
		min.	typ.	max.	
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	50	$^\circ C/W$
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}_{IGBT}$	-	-	0.347	
Thermal Resistance, FWD Junction to Case	$R_{th(j-c)}_{FWD}$	-	-	1.191	

■ Characteristics (Representative)

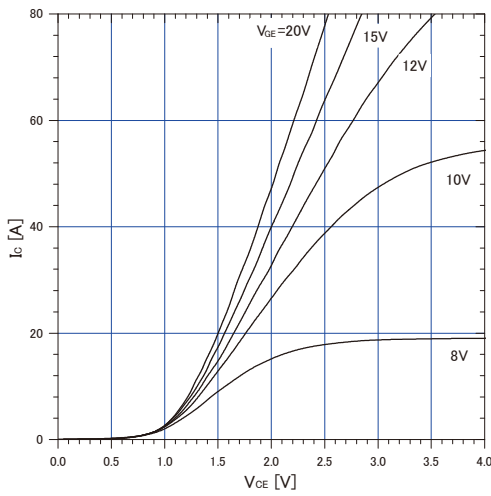
Graph.1
DC Collector Current vs T_c
 $V_{GE} \geq +15V, T_j \leq 175^\circ C$



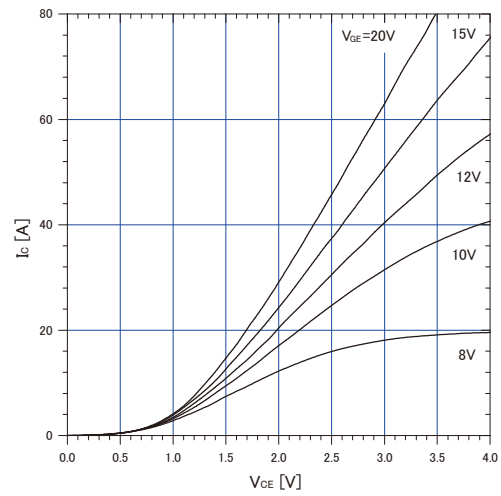
Graph.2
Collector Current vs. switching frequency
 $V_{GE} = +15V, T_c \leq 175^\circ C, V_{CC} = 600V, D = 0.5, R_g = 10\Omega, T_c = 100^\circ C$



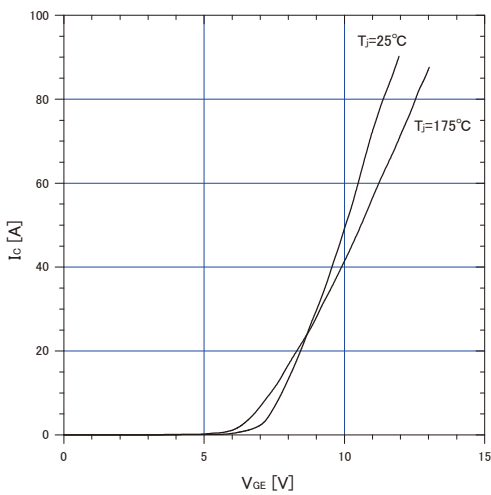
Graph.3
Typical Output Characteristics ($V_{CE} - I_c$)
 $T_j = 25^\circ C$



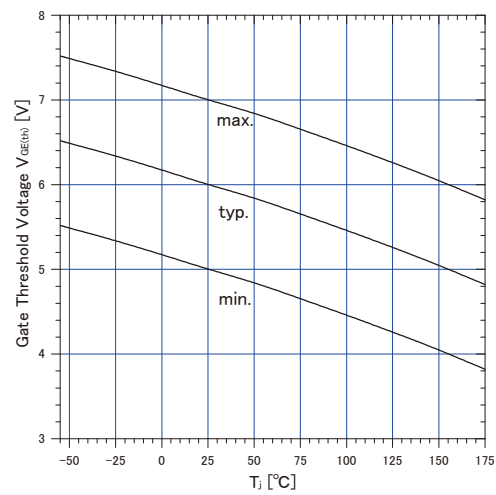
Graph.4
Typical Output Characteristics ($V_{CE} - I_c$)
 $T_j = 175^\circ C$



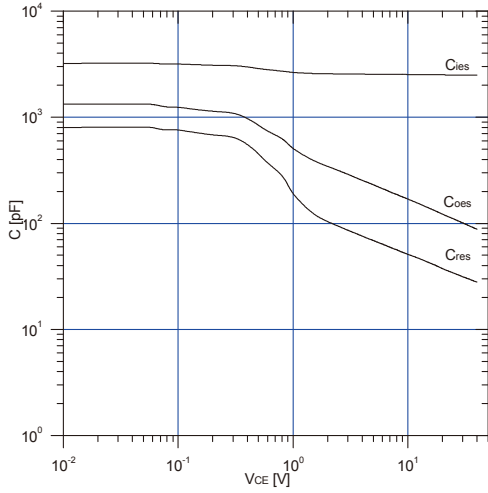
Graph.5
Typical Transfer Characteristics
 $V_{GE} = +15V$



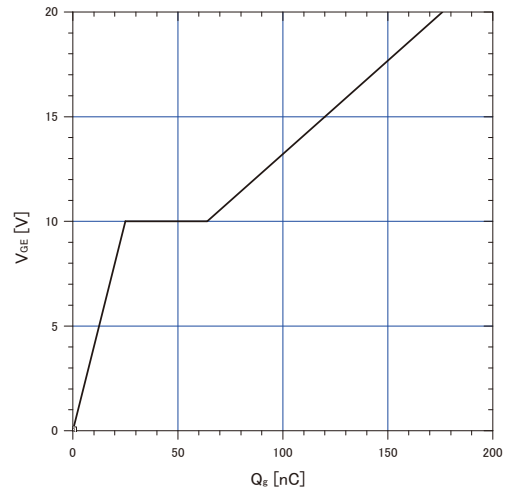
Graph.6
Gate Threshold Voltage vs. T_j
 $I_c = 40mA, V_{CE} = 20V$



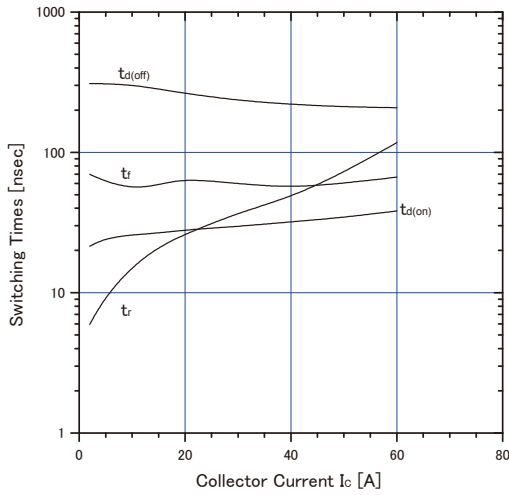
Graph.7
Typical Capacitance
 $V_{GE}=0V, f=1MHz, T_J=25^{\circ}C$



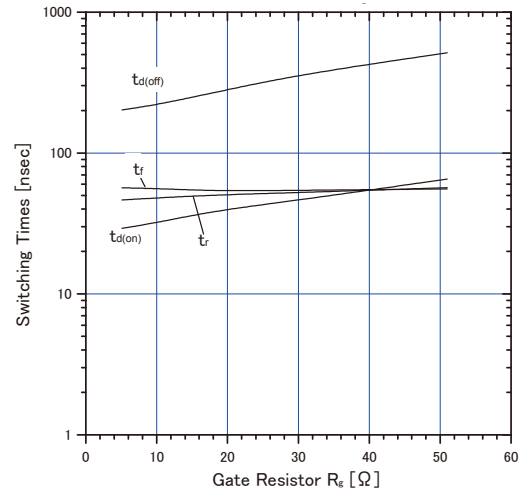
Graph.8
Typical Gate Charge
 $V_{cc}=600V, I_c=40A, T_J=25^{\circ}C$



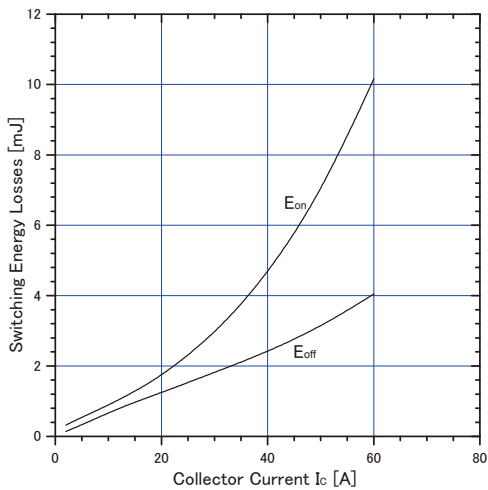
Graph.9
Typical switching time vs. Ic
 $T_J=175^{\circ}C, V_{cc}=600V, L=500\mu H$
 $V_{GE}=15V, R_g=10\Omega$



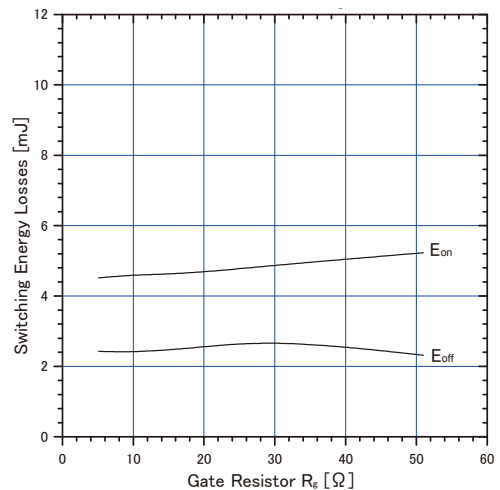
Graph.10
Typical switching time vs. Rg
 $T_J=175^{\circ}C, V_{cc}=600V, I_c=40A, L=500\mu H$
 $V_{GE}=15V$



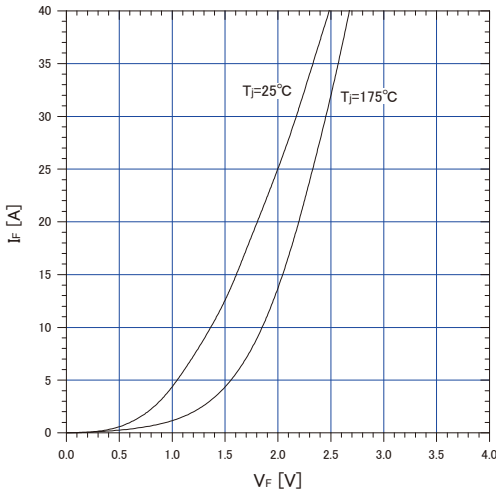
Graph.11
Typical switching losses vs. Ic
 $T_J=175^{\circ}C, V_{cc}=600V, L=500\mu H$
 $V_{GE}=15V, R_g=10\Omega$



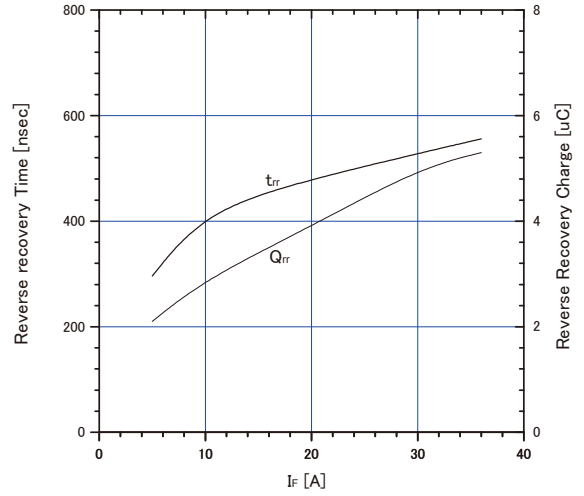
Graph.12
Typical switching losses vs. Rg
 $T_J=175^{\circ}C, V_{cc}=600V, I_c=40A, L=500\mu H$
 $V_{GE}=15V$



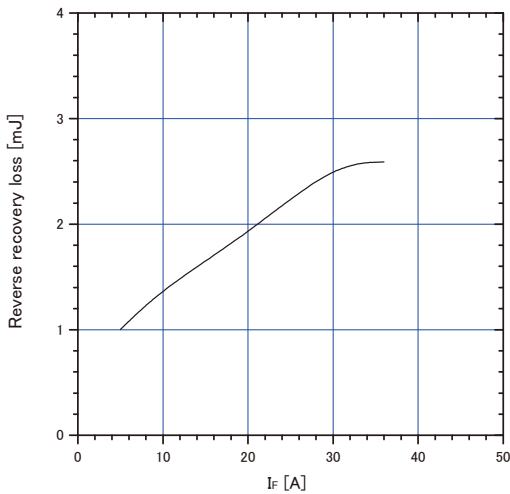
Graph.13
FWD Forward voltage drop (V_F-I_F)



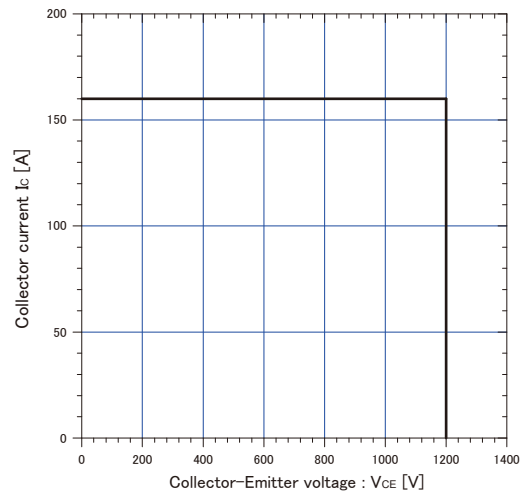
Graph.14
Typical reverse recovery characteristics vs. I_F
 $T_J=175^\circ\text{C}$, $V_{CC}=600\text{V}$, $L=500\mu\text{H}$,
 $V_{GE}=15\text{V}$, $R_G=10\Omega$



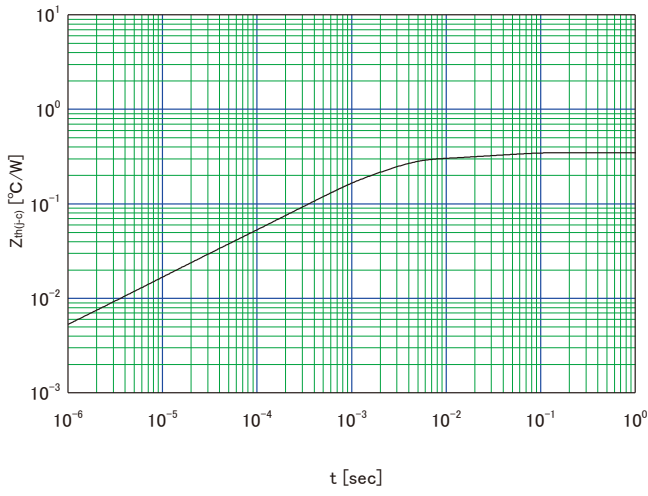
Graph.15
Typical reverse recovery loss vs. I_F
 $T_J=175^\circ\text{C}$, $V_{CC}=600\text{V}$, $L=500\mu\text{H}$
 $V_{GE}=15\text{V}$, $R_G=10\Omega$



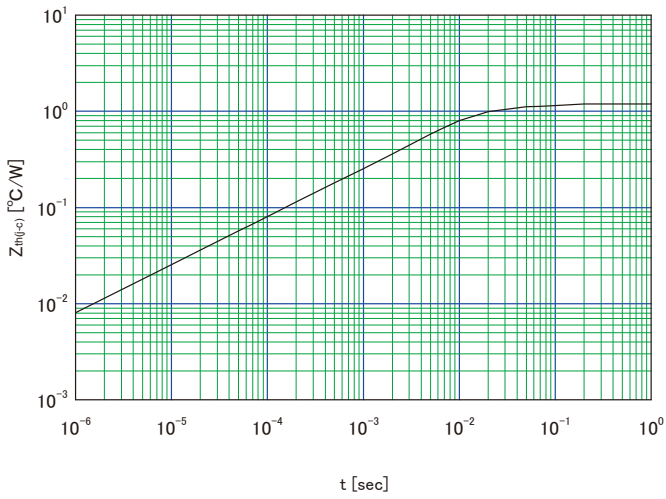
Graph.16
Reverse biased Safe Operating Area
 $T_J \leq 175^\circ\text{C}$, $V_{GE}=+15\text{V}/0\text{V}$, $R_G=10\Omega$



Graph.17
Transient thermal resistance of IGBT

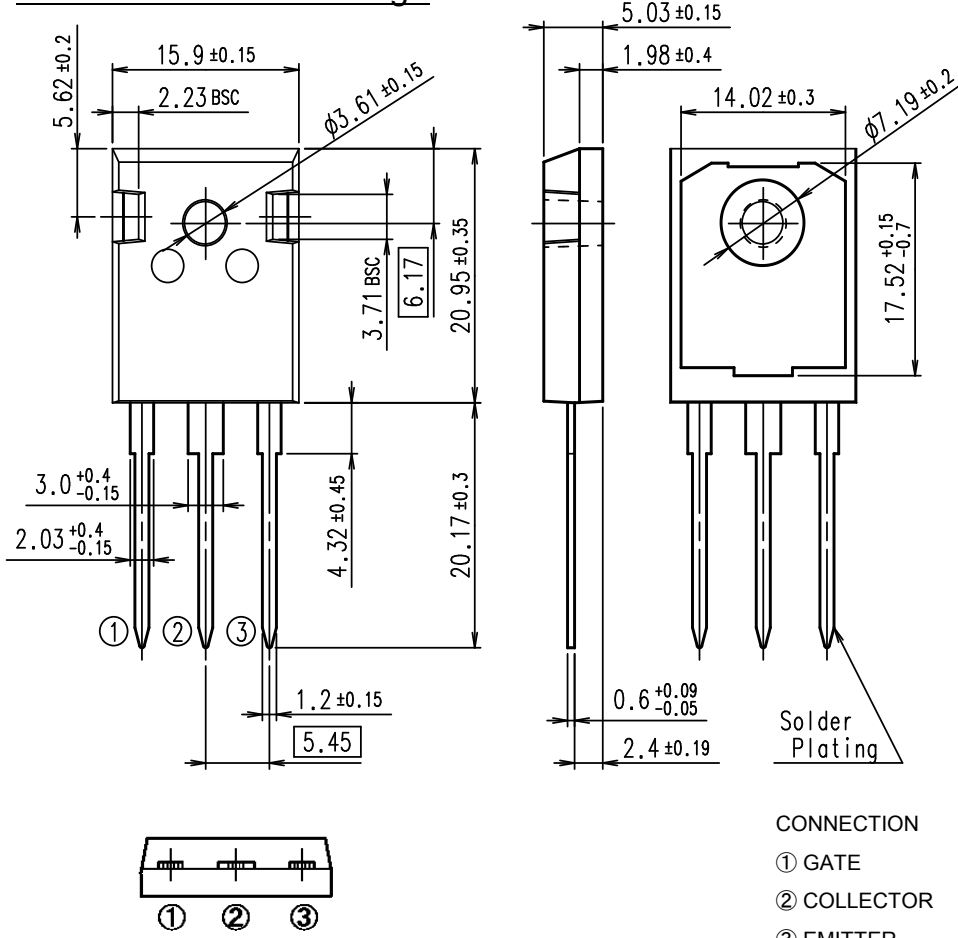


Graph.18
Transient thermal resistance of FWD



■ Outline Drawings, mm

Outview : TO-247 Package



DIMENSIONS ARE IN MILLIMETERS.

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